LMH6639 190MHz Rail-to-Rail Output Amplifier with Disable

Check for Samples: LMH6639

FEATURES

- **(V_S = 5V, Typical values unless specified)**
- **Supply current (no load) 3.6mA**
- **Supply current (off mode) 400µA**
- **Output resistance (closed loop 1MHz) 0.186Ω**
- **−3dB BW (A_V = 1) 190MHz**
- **Settling time 33nsec**
- **Input common mode voltage −0.2V to 4V**
- **Output voltage swing 40mV from rails**
- **Linear output current 110mA**
- **Total harmonic distortion −60dBc**
- **Fully characterized for 3V, 5V and ±5V**
- **No output phase reversal with CMVR exceeded**
- **Excellent overdrive recovery**
- **Off Isolation 1MHz −70dB**
- **Differential Gain 0.12%**
- **Differential Phase 0.045°**

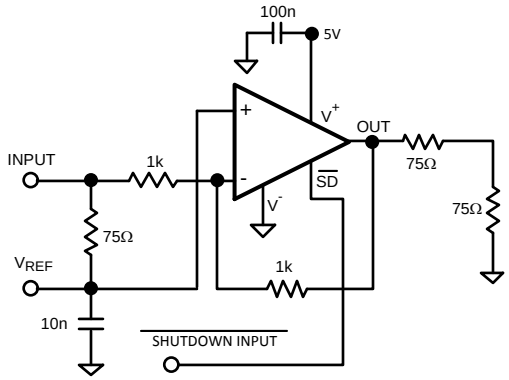
APPLICATIONS

- **Active filters**
- **CD/DVD ROM**
- **ADC buffer amplifier**
- **Portable video**
- **Current sense buffer**

DESCRIPTION

The LMH6639 is a voltage feedback operational amplifier with a rail-to-rail output drive capability of 110mA. Employing National's patented VIP10 process, the LMH6639 delivers a bandwidth of 190MHz at a current consumption of only 3.6mA. An input common mode voltage range extending to 0.2V below the V^- and to within 1V of V^+, makes the LMH6639 a true single supply op-amp. The output voltage range extends to within 30mV of either supply rail providing the user with a dynamic range that is especially desirable in low voltage applications.

The LMH6639 offers a slew rate of 172V/µs resulting in a full power bandwidth of approximately 28MHz. The LMH6639 also offers protection for the input transistors by using two anti-parallel diodes and a series resistor connected across the inputs. The T_{ON} value of 83nsec combined with a settling time of 33nsec makes this device ideally suited for multiplexing applications (see application note for details). Careful attention has been paid to ensure device stability under all operating voltages and modes. The result is a very well behaved frequency response characteristic for any gain setting including +1, and excellent specifications for driving video cables including harmonic distortion of −60dBc, differential gain of 0.12% and differential phase of 0.045°



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Absolute Maximum Ratings (1)

ESD Tolerance	2KV (2)
	200V (3)
V_{IN} Differential	±2.5V
Input Current	±10mA
Supply Voltage ($V^+ – V^-$)	13.5V
Voltage at Input/Output pins	V^+ +0.8V, V^- −0.8V
Storage Temperature Range	−65°C to +150°C
Junction Temperature (4)	+150°C
Soldering Information	
Infrared or Convection (20 sec)	235°C
Wave Soldering (10 sec)	260°C

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not guaranteed. For guaranteed specifications and the test conditions, see the Electrical Characteristics.
(2) Human body model, 1.5kΩ in series with 100pF.
(3) Machine Model, 0Ω in series with 200pF.
(4) The maximum power dissipation is a function of $T_{J(MAX)}$, θ_{JA}, and T_A. The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} - T_A)/ \theta_{JA}$. All numbers apply for packages soldered directly onto a PC board.

Operating Ratings (1)

Supply Voltage (V^+ to V^-)	3V to 12V
Operating Temperature Range (2)	−40°C to +85°C
Package Thermal Resistance (θ_{JA}) (2)	
SOT23-6	265°C/W
SOIC-8	190°C/W

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not guaranteed. For guaranteed specifications and the test conditions, see the Electrical Characteristics.
(2) The maximum power dissipation is a function of $T_{J(MAX)}$, θ_{JA}, and T_A. The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} - T_A)/ \theta_{JA}$. All numbers apply for packages soldered directly onto a PC board.

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3V Electrical Characteristics

Unless otherwise specified, all limits guaranteed for at T_J = 25°C, V^+ = 3V, V^- = 0V, $V_O = V_{CM} = V^+/2$, and R_L = 2kΩ to $V^+/2$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions		Min (1)	Typ (2)	Max (1)	Units
BW	−3dB BW	A_V = +1		120	170		MHz
		A_V = −1			63		
$BW_{0.1dB}$	0.1dB Gain Flatness	R_F = 2.65kΩ , R_L = 1kΩ,			16.4		MHz
FPBW	Full Power Bandwidth	A_V = +1, $V_{OUT} = 2V_{PP}$, −1dB V^+ = 1.8V, V^- = 1.2V			21		MHz
GBW	Gain Bandwidth product	A_V = +1			83		MHz
e_n	Input-Referred Voltage Noise	R_F = 33kΩ	f = 10kHz		19		$nV/\sqrt{Hz}$
			f = 1MHz		16		
i_n	Input-Referred Current Noise	R_F = 1MΩ	f = 10kHz		1.30		$pA/\sqrt{Hz}$
			f = 1MHz		0.36		
THD	Total Harmonic Distortion	f = 5MHz, $V_O = 2V_{PP}$, A_V = +2, R_L = 1kΩ to $V^+/2$			−50		dBc
T_S	Settling Time	$V_O = 2V_{PP}$, ±0.1%			37		ns
SR	Slew Rate	A_V = −1 (3)		120	167		V/µs
V_{OS}	Input Offset Voltage				1.01	5 **7**	mV
TC V_{OS}	Input Offset Average Drift	(4)			8		µV/°C
I_B	Input Bias Current	(5)			−1.02	−2.6 **−3.5**	µA
I_{OS}	Input Offset Current				20	800 **1000**	nA
R_{IN}	Common Mode Input Resistance	A_V = +1, f = 1kHz, R_S = 1MΩ			6.1		MΩ
C_{IN}	Common Mode Input Capacitance	A_V = +1, R_S = 100kΩ			1.35		pF
CMVR	Input Common-Mode Voltage Range	CMRR ≥ 50dB			−0.3	−0.2 **−0.1**	V
				1.8 **1.6**	2		
CMRR	Common Mode Rejection Ratio	(6)		72	93		dB
A_{VOL}	Large Signal Voltage Gain	$V_O = 2V_{PP}$, R_L = 2kΩ to $V^+/2$		80 **76**	100		dB
		$V_O = 2V_{PP}$, R_L = 150Ω to $V^+/2$		74 **70**	78		
V_O	Output Swing High	R_L = 2kΩ to $V^+/2$, V_{ID} = 200mV		2.90	2.98		V
		R_L = 150Ω to $V^+/2$, V_{ID} = 200mV		2.75	2.93		
		R_L = 50Ω to $V^+/2$, V_{ID} = 200mV		2.6	2.85		
	Output Swing Low	R_L = 2kΩ to $V^+/2$, V_{ID} = −200mV			25	75	mV
		R_L = 150Ω to $V^+/2$, V_{ID} = −200mV			75	200	
		R_L = 50Ω to $V^+/2$, V_{ID} = −200mV			130	300	
I_{SC}	Output Short Circuit Current	Sourcing to $V^+/2$, (7)		50 **35**	120		mA
		Sinking to $V^+/2$, (7)		67 **40**	140		
I_{OUT}	Output Current	V_O = 0.5V from either supply			99		mA

(1) All limits are guaranteed by testing or statistical analysis.
(2) Typical values represent the most likely parametric norm.
(3) Slew rate is the average of the rising and falling slew rates.
(4) Offset voltage average drift determined by dividing the change in V_{OS} at temperature extremes into the total temperature change.
(5) Positive current corresponds to current flowing into the device.
(6) f ≤ 1kHz (see typical performance Characteristics)
(7) Short circuit test is a momentary test.

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3V Electrical Characteristics (continued)

Unless otherwise specified, all limits guaranteed for at T_J = 25°C, V^+ = 3V, V^- = 0V, $V_O = V_{CM} = V^+/2$, and R_L = 2kΩ to $V^+/2$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min (1)	Typ (2)	Max (1)	Units
PSRR	Power Supply Rejection Ratio	(6)	72	96		dB
I_S	Supply Current (Enabled)	No Load		3.5	5.6 **7.5**	mA
	Supply Current (Disabled)			0.3	0.5 **0.7**	
TH_SD	Threshold Voltage for Shutdown Mode			V^+−1.59		V
I_SD PIN	Shutdown Pin Input Current	SD Pin Connect to 0V (5)		−13		µA
T_{ON}	On Time After Shutdown			83		nsec
T_{OFF}	Off Time to Shutdown			160		nsec
R_{OUT}	Output Resistance Closed Loop	R_F = 10kΩ, f = 1kHz, A_V = −1		27		mΩ
		R_F = 10kΩ, f = 1MHz, A_V = −1		266		

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5V Electrical Characteristics

Unless otherwise specified, all limits guaranteed for at T_J = 25°C, V^+ = 5V, V^- = 0V, $V_O = V_{CM} = V^+/2$, and R_L = 2kΩ to $V^+/2$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions		Min (1)	Typ (2)	Max (1)	Units
BW	−3dB BW	A_V = +1		130	190		MHz
		A_V = −1			64		
$BW_{0.1dB}$	0.1dB Gain Flatness	R_F = 2.51kΩ, R_L = 1kΩ,			16.4		MHz
FPBW	Full Power Bandwidth	A_V = +1, V_{OUT} = $2V_{PP}$, −1dB			28		MHz
GBW	Gain Bandwidth Product	A_V = +1			86		MHz
e_n	Input-Referred Voltage Noise	R_F = 33kΩ	f = 10kHz		19		$nV/\sqrt{Hz}$
			f = 1MHz		16		
i_n	Input-Referred Current Noise	R_F = 1MΩ	f = 10KHz		1.35		$pA/\sqrt{Hz}$
			f = 1MHz		0.35		
THD	Total Harmonic Distortion	f = 5MHz, V_O = $2V_{PP}$, A_V = +2 R_L = 1kΩ to $V^+/2$			−60		dBc
DG	Differential Gain	NTSC, A_V = +2 R_L = 150Ω to $V^+/2$			0.12		%
DP	Differential Phase	NTSC, A_V = +2 R_L = 150Ω to $V^+/2$			0.045		deg
T_S	Settling Time	V_O = $2V_{PP}$, ±0.1%			33		ns
SR	Slew Rate	A_V = −1, (3)		130	172		V/µs
V_{OS}	Input Offset Voltage				1.02	5 **7**	mV
TC V_{OS}	Input Offset Average Drift	(4)			8		µV/°C
I_B	Input Bias Current	(5)			−1.2	−2.6 **−3.25**	µA
I_{OS}	Input Offset Current				20	800 **1000**	nA
R_{IN}	Common Mode Input Resistance	A_V = +1, f = 1kHz, R_S = 1MΩ			6.88		MΩ
C_{IN}	Common Mode Input Capacitance	A_V = +1, R_S = 100kΩ			1.32		pF
CMVR	Common-Mode Input Voltage Range	CMRR ≥ 50dB			−0.3	−0.2 **−0.1**	V
					4	3.8 **3.6**	
CMRR	Common Mode Rejection Ratio	(6)		72	95		dB
A_{VOL}	Large Signal Voltage Gain	V_O = $4V_{PP}$ R_L = 2kΩ to $V^+/2$		86 **82**	100		dB
		V_O = $3.75V_{PP}$ R_L = 150Ω to $V^+/2$		74 **70**	77		
V_O	Output Swing High	R_L = 2kΩ to $V^+/2$, V_{ID} = 200mV		4.90	4.97		V
		R_L = 150Ω to $V^+/2$, V_{ID} = 200mV		4.65	4.90		
		R_L = 50Ω to $V^+/2$, V_{ID} = 200mV		4.40	4.77		
	Output Swing Low	R_L = 2kΩ to $V^+/2$, V_{ID} = −200mV			25	100	mV
		R_L = 150Ω to $V^+/2$, V_{ID} = −200mV			85	200	
		R_L = 50Ω to $V^+/2$, V_{ID} = −200mV			190	400	

(1) All limits are guaranteed by testing or statistical analysis.
(2) Typical values represent the most likely parametric norm.
(3) Slew rate is the average of the rising and falling slew rates.
(4) Offset voltage average drift determined by dividing the change in V_{OS} at temperature extremes into the total temperature change.
(5) Positive current corresponds to current flowing into the device.
(6) f ≤ 1kHz (see typical performance Characteristics)

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5V Electrical Characteristics (continued)

Unless otherwise specified, all limits guaranteed for at T_J = 25°C, V^+ = 5V, V^- = 0V, V_O = V_{CM} = $V^+/2$, and R_L = 2kΩ to $V^+/2$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min (1)	Typ (2)	Max (1)	Units
I_{SC}	Output Short Circuit Current	Sourcing to $V^+/2$, (7)	100 **79**	160		mA
		Sinking from $V^+/2$, (7)	120 **85**	190		
I_{OUT}	Output Current	V_O = 0.5V from either supply		110		mA
PSRR	Power Supply Rejection Ratio	(6)	72	96		dB
I_S	Supply Current (Enabled)	No Load		3.6	5.8 **8.0**	mA
	Supply Current (Disabled)			0.40	0.8 **1.0**	
TH_SD	Threshold Voltage for Shutdown Mode			V^+ −1.65		V
I_SD PIN	Shutdown Pin Input Current	SD Pin Connected to 0V (5)		−30		µA
T_{ON}	On Time after Shutdown			83		nsec
T_{OFF}	Off Time to Shutdown			160		nsec
R_{OUT}	Output Resistance Closed Loop	R_F = 10kΩ, f = 1kHz, A_V = −1		29		mΩ
		R_F = 10kΩ, f = 1MHz, A_V = −1		253		

(7) Short circuit test is a momentary test.

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±5V Electrical Characteristics

Unless otherwise specified, all limits guaranteed for at T_J = 25°C, V_{SUPPLY} = ±5V, V_O = V_{CM} = GND, and R_L = 2kΩ to V^+/2. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions		Min (1)	Typ (2)	Max (1)	Units
BW	−3dB BW	A_V = +1		150	228		MHz
		A_V = −1			65		
$BW_{0.1dB}$	0.1dB Gain Flatness	R_F = 2.26kΩ, R_L = 1kΩ			18		MHz
FPBW	Full Power Bandwidth	A_V = +1, V_{OUT} = $2V_{PP}$, −1dB			29		MHz
GBW	Gain Bandwidth Product	A_V = +1			90		MHz
e_n	Input-Referred Voltage Noise	R_F = 33kΩ	f = 10kHz		19		$nV/\sqrt{Hz}$
			f = 1MHz		16		
i_n	Input-Referred Current Noise	R_F = 1MΩ	f = 10kHz		1.13		$pA/\sqrt{Hz}$
			f = 1MHz		0.34		
THD	Total Harmonic Distortion	f = 5MHz, V_O = $2V_{PP}$, A_V = +2, R_L = 1kΩ			−71.2		dBc
DG	Differential Gain	NTSC, A_V = +2 R_L = 150Ω			0.11		%
DP	Differential Phase	NTSC, A_V = +2 R_L = 150Ω			0.053		deg
T_S	Settling Time	V_O = $2V_{PP}$, ±0.1%			33		ns
SR	Slew Rate	A_V = −1 (3)		140	200		V/µs
V_{OS}	Input Offset Voltage				1.03	5 **7**	mV
TC V_{OS}	Input Offset Voltage Drift	(4)			8		µV/°C
I_B	Input Bias Current	(5)			−1.40	−2.6 **−3.25**	µA
I_{OS}	Input Offset Current				20	800 **1000**	nA
R_{IN}	Common Mode Input Resistance	A_V +1, f = 1kHz, R_S = 1MΩ			7.5		MΩ
C_{IN}	Common Mode Input Capacitance	A_V = +1, R_S = 100kΩ			1.28		pF
CMVR	Common Mode Input Voltage Range	CMRR ≥ 50dB			−5.3	−5.2 **−5.1**	V
				3.8 **3.6**	4.0		
CMRR	Common Mode Rejection Ratio	(6)		72	95		dB
A_{VOL}	Large Signal Voltage Gain	V_O = $9V_{PP}$, R_L = 2kΩ		88 **84**	100		dB
		V_O = $8V_{PP}$, R_L = 150Ω		74 **70**	77		
V_O	Output Swing High	R_L = 2kΩ, V_{ID} = 200mV		4.85	4.96		V
		R_L = 150Ω, V_{ID} = 200mV		4.55	4.80		
		R_L = 50Ω, V_{ID} = 200mV		3.60	4.55		
	Output Swing Low	R_L = 2kΩ, V_{ID} = −200mV			−4.97	−4.90	V
		R_L = 150Ω, V_{ID} = −200mV			−4.85	−4.55	
		R_L = 50Ω, V_{ID} = −200mV			−4.65	−4.30	

(1) All limits are guaranteed by testing or statistical analysis.
(2) Typical values represent the most likely parametric norm.
(3) Slew rate is the average of the rising and falling slew rates.
(4) Offset voltage average drift determined by dividing the change in V_{OS} at temperature extremes into the total temperature change.
(5) Positive current corresponds to current flowing into the device.
(6) f ≤ 1kHz (see typical performance Characteristics)

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±5V Electrical Characteristics (continued)

Unless otherwise specified, all limits guaranteed for at T_J = 25°C, V_{SUPPLY} = ±5V, V_O = V_{CM} = GND, and R_L = 2kΩ to $V^+/2$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min (1)	Typ (2)	Max (1)	Units
I_{SC}	Output Short Circuit Current	Sourcing to Ground, (7)	100 **80**	168		mA
		Sinking to Ground, (7)	110 **85**	190		
I_{OUT}	Output Current	V_O = 0.5V from either supply		112		mA
PSRR	Power Supply Rejection Ratio	(6)	72	96		dB
I_S	Supply Current (Enabled)	No Load		4.18	6.5 **8.5**	mA
	Supply Current (Disabled)			0.758	1.0 **1.3**	
TH_SD	Threshold Voltage for Shutdown Mode			V^+ − 1.67		V
I_SD PIN	Shutdown Pin Input Current	SD Pin Connected to −5V (5)		−84		µA
T_{ON}	On Time after Shutdown			83		nsec
T_{OFF}	Off Time to Shutdown			160		nsec
R_{OUT}	Output Resistance Closed Loop	R_F = 10kΩ, f = 1kHz, A_V = −1		32		mΩ
		R_F = 10kΩ, f = 1MHz, A_V = −1		226		

(7) Short circuit test is a momentary test.

Connection Diagram

SOT23-6

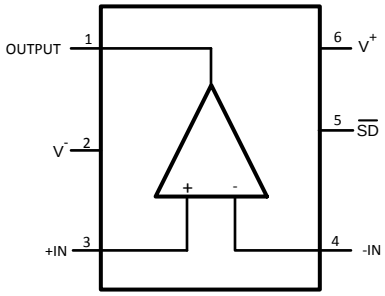

Figure 1. Top View

SOIC-8

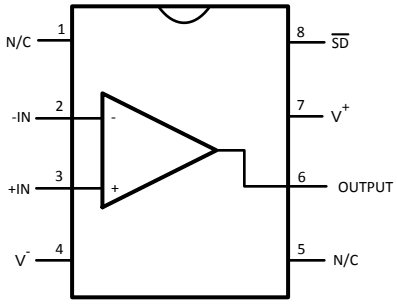

Figure 2. Top View

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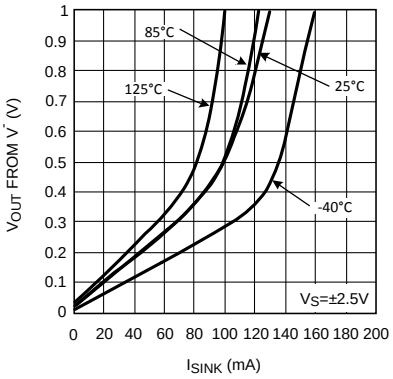
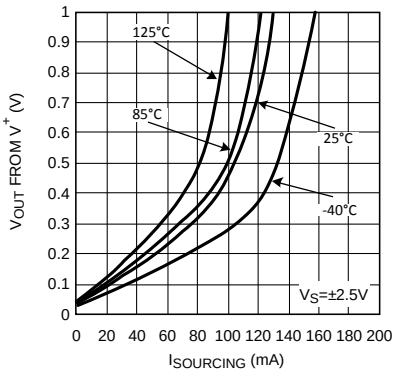
Typical Performance Characteristics

At T_J = 25°C, V^+ = +2.5, V^- = −2.5V, R_F = 330Ω for A_V = +2, R_F = 1kΩ for A_V = −1. Unless otherwise specified.

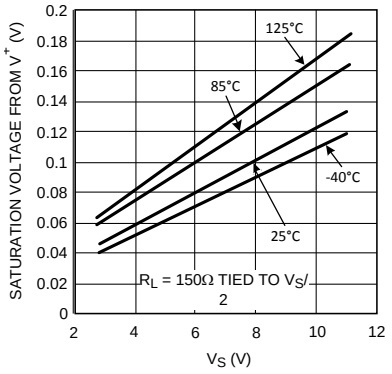
Output Sinking Saturation Voltage vs. I_{OUT} for Various Temperature



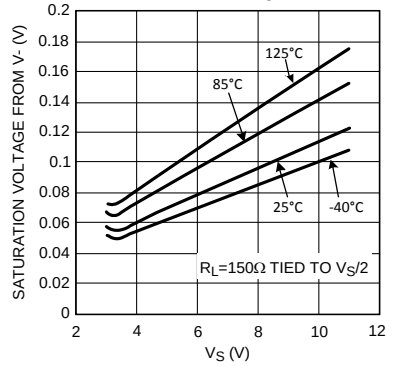
Output Sourcing Saturation Voltage vs. I_{OUT} for Various Temperature



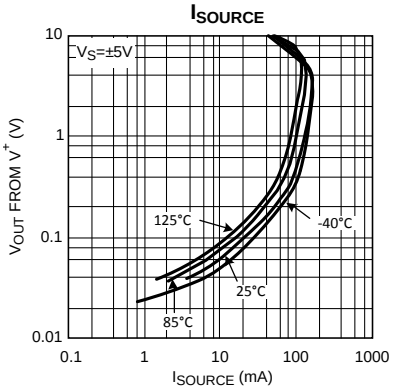
Positive Output Saturation Voltage vs. V_{SUPPLY} for Various Temperature



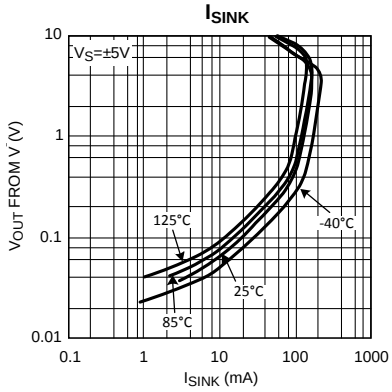
Negative Output Saturation Voltage vs. V_{SUPPLY} for Various Temperature



V_{OUT} from V^+ vs. I_{SOURCE}



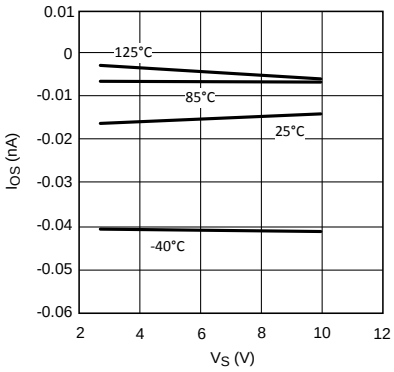
V_{OUT} from V^- vs. I_{SINK}



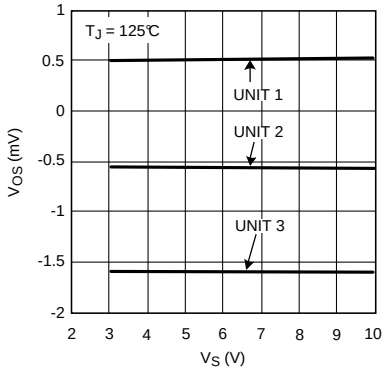
Typical Performance Characteristics (continued)

At T_J = 25°C, V^+ = +2.5, V^- = −2.5V, R_F = 330Ω for A_V = +2, R_F = 1kΩ for A_V = −1. Unless otherwise specified.

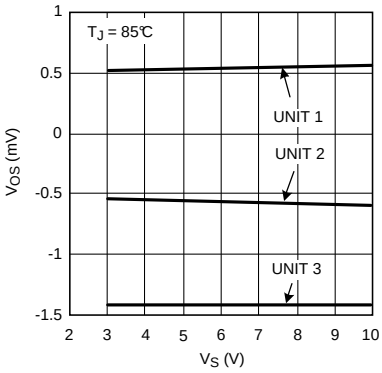
I_{OS} vs. V_S for Various Temperature



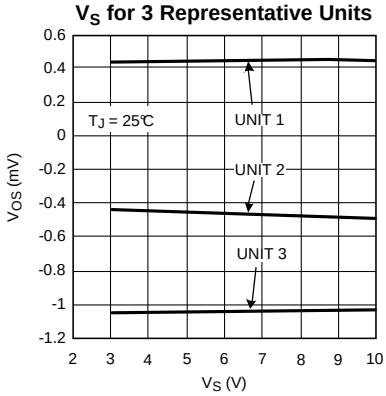
V_{OS} vs. V_S for 3 Representative Units



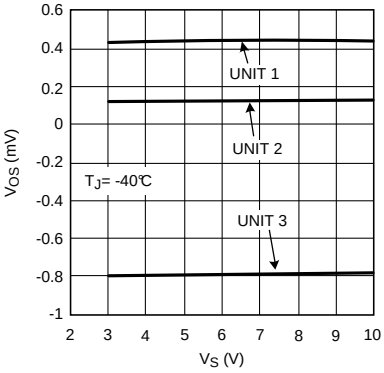
V_{OS} vs. V_S for 3 Representative Units



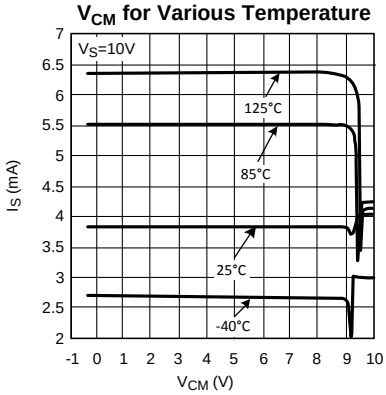
V_{OS} vs. V_S for 3 Representative Units



V_{OS} vs. V_S for 3 Representative Units



I_{SUPPLY} vs. V_{CM} for Various Temperature



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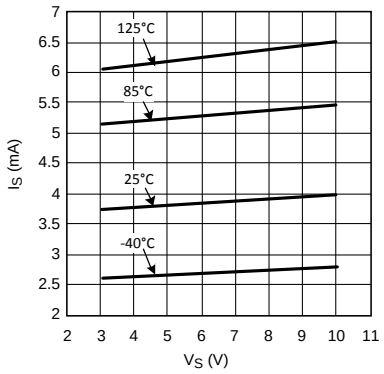
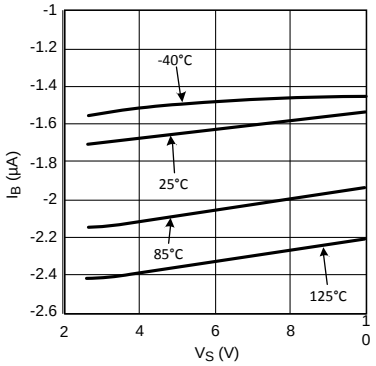
Typical Performance Characteristics (continued)

At T_J = 25°C, V^+ = +2.5, V^- = −2.5V, R_F = 330Ω for A_V = +2, R_F = 1kΩ for A_V = −1. Unless otherwise specified.

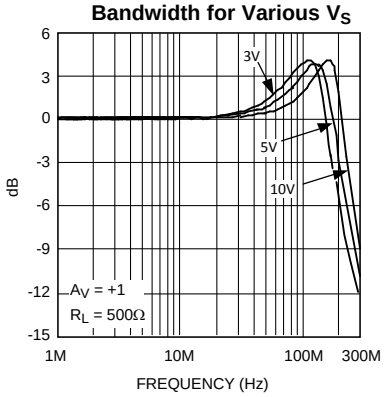
I_{SUPPLY} vs. V_S for Various Temperature



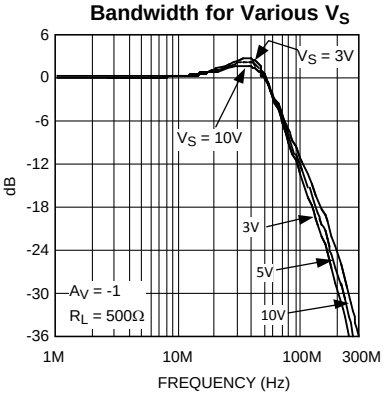
I_B vs. V_S for Various Temperature



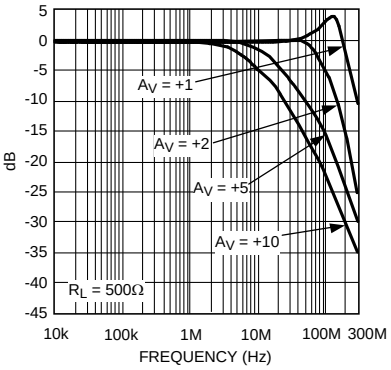
Bandwidth for Various V_S



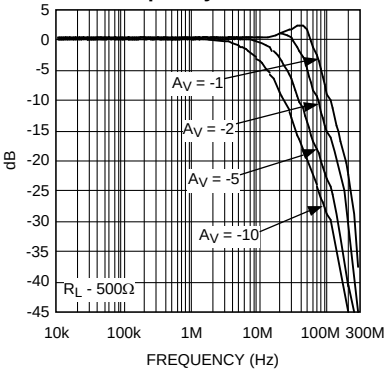
Bandwidth for Various V_S



Gain vs. Frequency Normalized



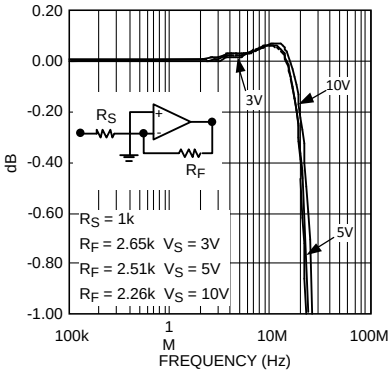
Gain vs. Frequency Normalized



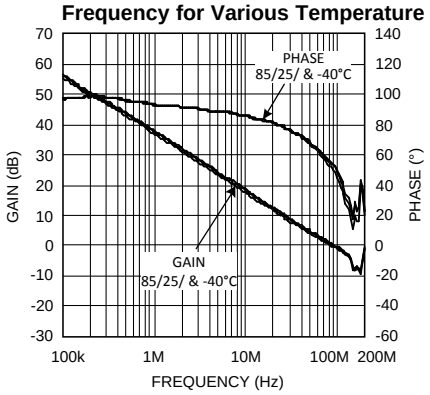
Typical Performance Characteristics (continued)

At T_J = 25°C, V^+ = +2.5, V^- = −2.5V, R_F = 330Ω for A_V = +2, R_F = 1kΩ for A_V = −1. Unless otherwise specified.

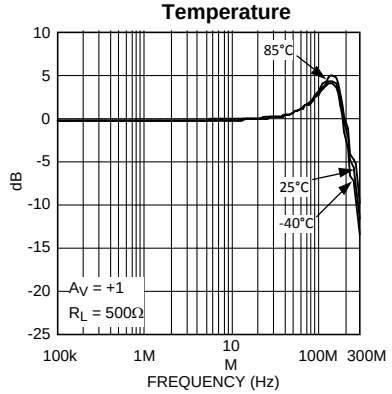
0.1dB Gain Flatness



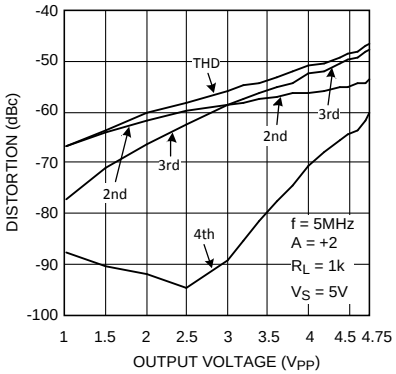
Gain and phase vs. Frequency for Various Temperature



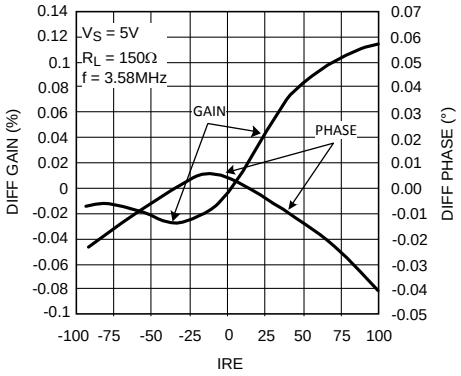
Frequency Response vs. Temperature



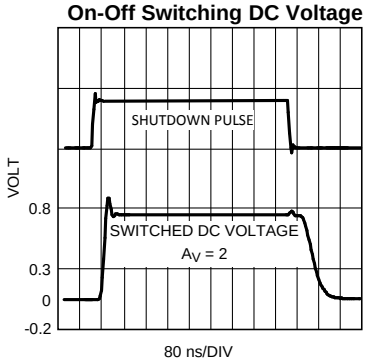
Harmonic Distortion



Differential Gain/Phase



On-Off Switching DC Voltage



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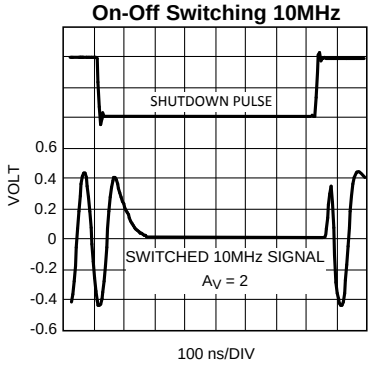
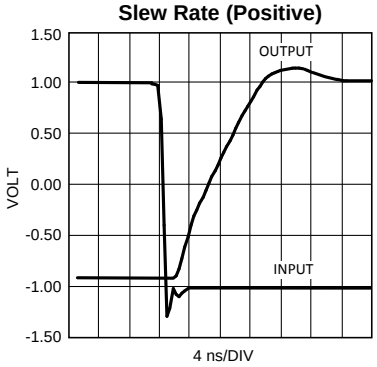
Typical Performance Characteristics (continued)

At T_J = 25°C, V^+ = +2.5, V^- = −2.5V, R_F = 330Ω for A_V = +2, R_F = 1kΩ for A_V = −1. Unless otherwise specified.

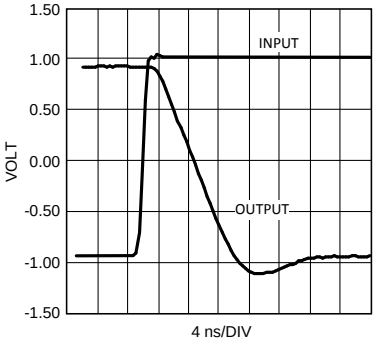
On-Off Switching 10MHz



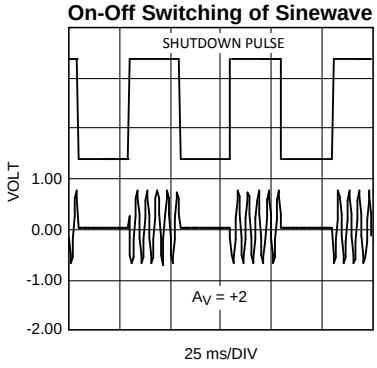
Slew Rate (Positive)



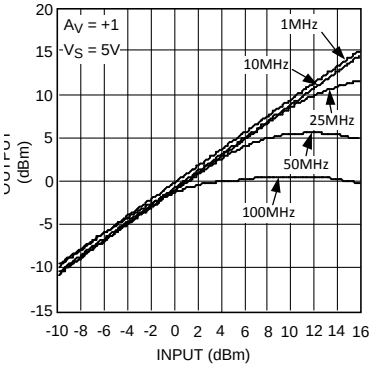
Slew Rate (Negative)



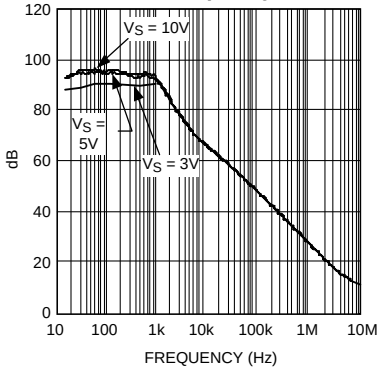
On-Off Switching of Sinewave



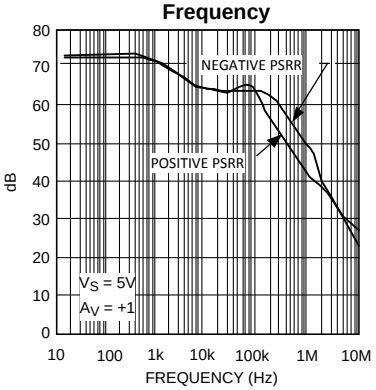
Power Sweep



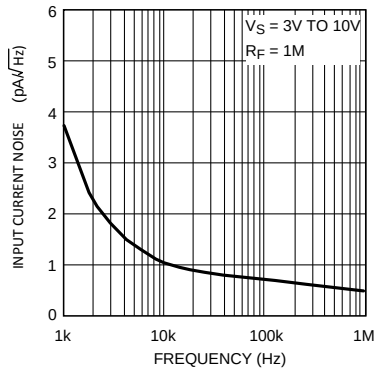
CMRR vs. Frequency



PSRR vs. Frequency



Current Noise



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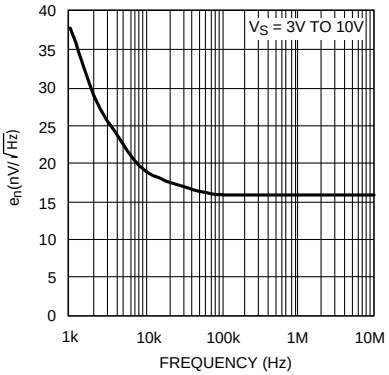
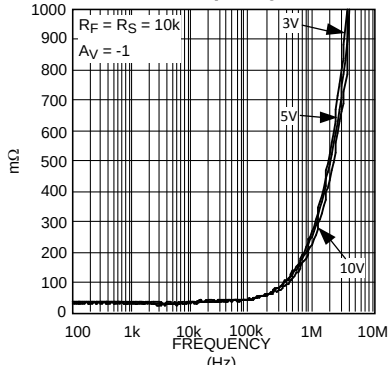
Typical Performance Characteristics (continued)

At T_J = 25°C, V^+ = +2.5, V^- = −2.5V, R_F = 330Ω for A_V = +2, R_F = 1kΩ for A_V = −1. Unless otherwise specified.

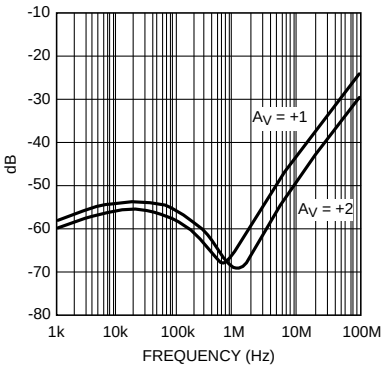
Voltage Noise



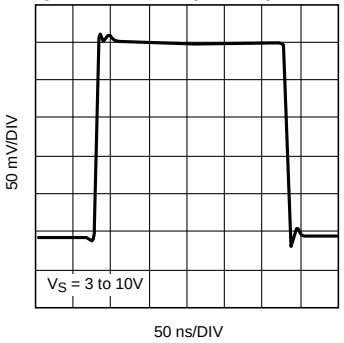
Closed Loop Output Resistance vs. Frequency



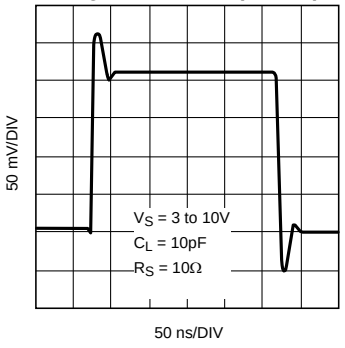
Off Isolation



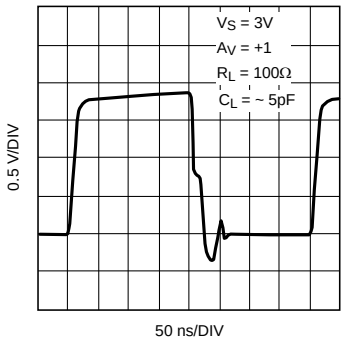
Small Signal Pulse Response (A_V = +1, R_L = 2k)



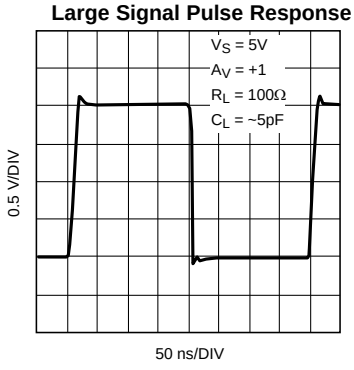
Small Signal Pulse Response (A_V = −1)



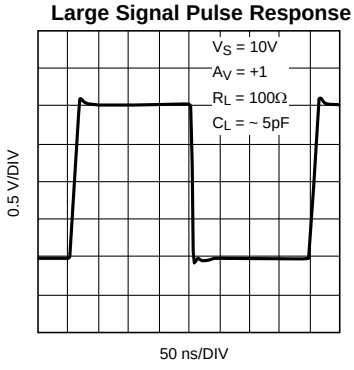
Large Signal Pulse Response (R_L = 2k)



Large Signal Pulse Response



Large Signal Pulse Response



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Application Notes

INPUT AND OUTPUT TOPOLOGY

All input / output pins are protected against excessive voltages by ESD diodes connected to V+ and V- rails (see Figure 3). These diodes start conducting when the input / output pin voltage approaches $1V_{be}$ beyond V+ or V- to protect against over voltage. These diodes are normally reverse biased. Further protection of the inputs is provided by the two resistors (R in Figure 3), in conjunction with the string of anti-parallel diodes connected between both bases of the input stage. The combination of these resistors and diodes reduces excessive differential input voltages approaching $2V_{be}$. The most common situation when this occurs is when the device is put in shutdown and the LMH6639's inputs no longer follow each other. In such a case, the diodes may conduct. As a consequence, input current increases, and a portion of signal may appear at the Hi-Z output. Another possible situation for the conduction of these diodes is when the LMH6639 is used as a comparator (or with little or no feedback). In either case, it is important to make sure that the subsequent current flow through the device input pins does not violate the Absolute Maximum Ratings of the device. To limit the current through the protection circuit extra series resistors can be placed. Together with the build in series resistors of several hundred ohms this extra resistors can limit the input current to a safe number depending on the used application. Be aware of the effect that extra series resistors may impact the switching speed of the device. A special situation occurs when the part is configured for a gain of +1, which means the output is directly connected to the inverting input, see Figure 4. When the part is now placed in shutdown mode the output comes in a high impedance state and is unable to keep the inverting input at the same level as the non-inverting input. In many applications the output is connected to the ground via a low impedance resistor. When this situation occurs and there is a DC voltage offset of more than 2 volt between the non-inverting input and the output, current flows from the non-inverting input through the series resistors R via the bypass diodes to the output. Now the input current becomes much bigger than expected and in many cases the source at the input cannot deliver this current and will drop down. Be sure in this situation that no DC current path is available from the non-inverting input to the output pin, or from the output pin to the load resistor. This DC path is drawn by a curved line and can be broken by placing one of the capacitors C_{IN} or C_{OUT} or both, depending on the used application.

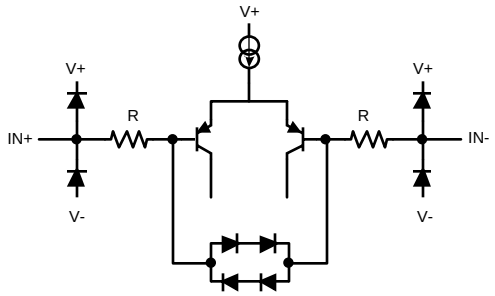

Figure 3.

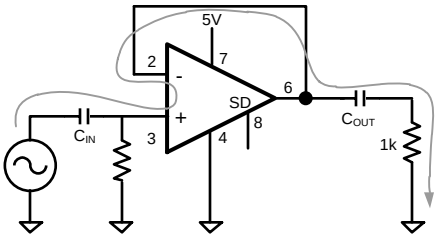

Figure 4. DC path while in shutdown

MULTIPLEXING 5 AND 10MHz

The LMH6639 may be used to implement a circuit which multiplexes two signals of different frequencies. Three LMH6639 high speed op-amps are used in the circuit of Figure 5 to accomplish the multiplexing function. Two LMH6639 are used to provide gain for the input signals, and the third device is used to provide output gain for the selected signal.

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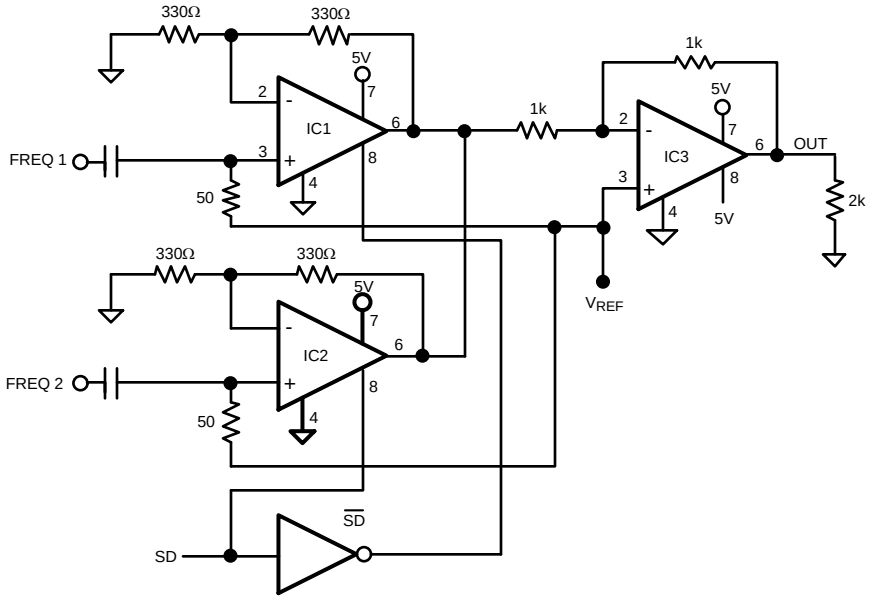

Note: Pin numbers pertain to SOIC-8 package

Figure 5. Multiplexer

Multiplexing signals “FREQ 1” and “FREQ 2” exhibit closed loop non-inverting gain of +2 each based upon identical 330Ω resistors in the gain setting positions of IC1 and IC2. The two multiplexing signals are combined at the input of IC3, which is the third LMH6639. This amplifier may be used as a unity gain buffer or may be used to set a particular gain for the circuit.

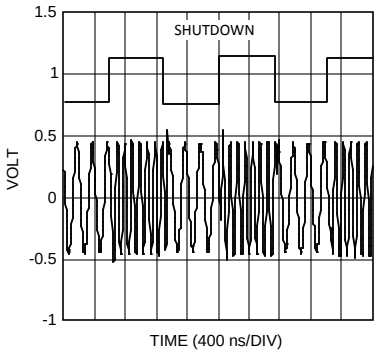

Figure 6. Switching between 5 and 10MHz

1k resistors are used to set an inverting gain of −1 for IC3 in the circuit of Figure 5. Figure 6 illustrates the waveforms produced. The upper trace shows the switching waveform used to switch between the 5MHz and 10MHz multiplex signals. The lower trace shows the output waveform consisting of 5MHz and 10MHz signals corresponding to the high or low state of the switching signal.

In the circuit of Figure 5, the outputs of IC1 and IC2 are tied together such that their output impedances are placed in parallel at the input of IC3. The output impedance of the disabled amplifier is high compared both to the output impedance of the active amplifier and the 330Ω gain setting resistors. The closed loop output resistance for the LMH6639 is around 0.2Ω. Thus the active state amplifier output impedance dominates the input node to IC3, while the disabled amplifier is assured of a high level of suppression of unwanted signals which might be present at the output.

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SHUTDOWN OPERATION

With $\overline{SD}$ pin left floating, the device enters normal operation. However, since the $\overline{SD}$ pin has high input impedance, it is best tied to V^+ for normal operation. This will avoid inadvertent shutdown due to capacitive pick-up from nearby nodes. LMH6639 will typically go into shutdown when $\overline{SD}$ pin is more than 1.7V below V^+, regardless of operating supplies.

The $\overline{SD}$ pin can be driven by push-pull or open collector (open drain) output logic. Because the LMH6639's shutdown is referenced to V+, interfacing to the shutdown logic is rather simple, for both single and dual supply operation, with either form of logic used. Typical configurations are shown in Figure 7 and Figure 8 below for push-pull output:

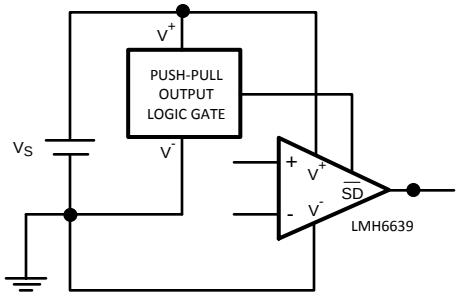

Figure 7. Shutdown Interface (Single Supply)

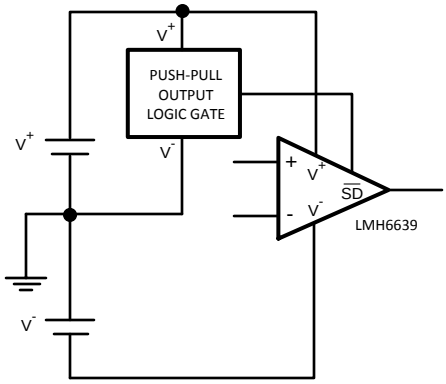

Figure 8. Shutdown Interface (Dual Supplies)

Common voltages for logic gates are +5V or +3V. To ensure proper power on/off with these supplies, the logic should be able to swing to 3.4V and 1.4V minimum, respectively.

LMH6639's shutdown pin can also be easily controlled in applications where the analog and digital sections are operated at different supplies. Figure 9 shows a configuration where a logic output, SD, can turn the LMH6639 on and off, independent of what supplies are used for the analog and the digital sections:

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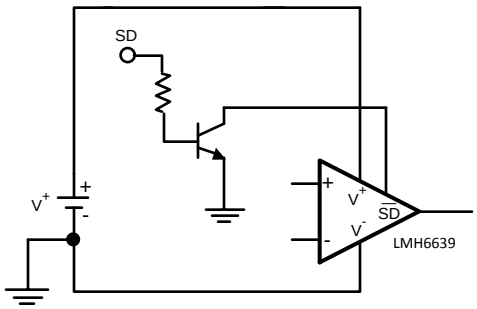

Figure 9. Shutdown Interface (Single Supply, Open Collector Logic)

The LMH6639 has an internal pull-up resistor on $\overline{SD}$ such that if left un-connected, the device will be in normal operation. Therefore, no pull-up resistor is needed on this pin. Another common application is where the transistor in Figure 9 above, would be internal to an open collector (open drain) logic gate; the basic connections will remain the same as shown.

PCB LAYOUT CONSIDERATION AND COMPONENTS SELECTION

Care should be taken while placing components on a PCB. All standard rules should be followed especially the ones for high frequency and/ or high gain designs. Input and output pins should be separated to reduce cross-talk, especially under high gain conditions. A groundplane will be helpful to avoid oscillations. In addition, a ground plane can be used to create micro-strip transmission lines for matching purposes. Power supply, as well as shutdown pin de-coupling will reduce cross-talk and chances of oscillations.

Another important parameter in working with high speed amplifiers is the component values selection. Choosing high value resistances reduces the cut-off frequency because of the influence of parasitic capacitances. On the other hand choosing the resistor values too low could "load down" the nodes and will contribute to higher overall power dissipation. Keeping resistor values at several hundreds of ohms up to several kΩ will offer good performance.

National Semiconductor suggests the following evaluation boards as a guide for high frequency layout and as an aid in device testing and characterization:

Device	Package	Evaluation Board PN
LMH6639MA	8-Pin SOIC	CLC730027
LMH6639MF	SOT23-6	CLC730116

These free evaluation boards are shipped when a device sample request is placed with National Semiconductor. For normal operation, tie the SD pin to V^+.

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Samples (Requires Login)
LMH6639MA	ACTIVE	SOIC	D	8	95	TBD	CU SNPB	Level-1-235C-UNLIM	
LMH6639MA/NOPB	ACTIVE	SOIC	D	8	95	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	
LMH6639MAX/NOPB	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	
LMH6639MF	ACTIVE	SOT-23	DBV	6	1000	TBD	CU SNPB	Level-1-260C-UNLIM	
LMH6639MF/NOPB	ACTIVE	SOT-23	DBV	6	1000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	
LMH6639MFX	ACTIVE	SOT-23	DBV	6	3000	TBD	CU SNPB	Level-1-260C-UNLIM	
LMH6639MFX/NOPB	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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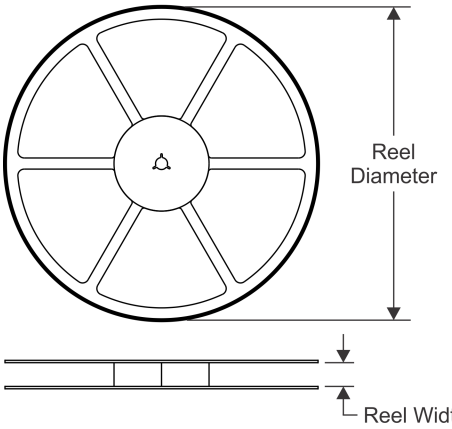
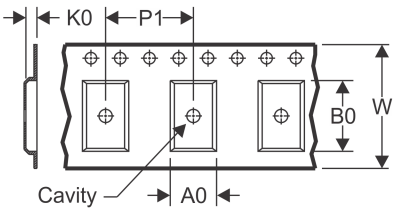
TAPE AND REEL INFORMATION

REEL DIMENSIONS

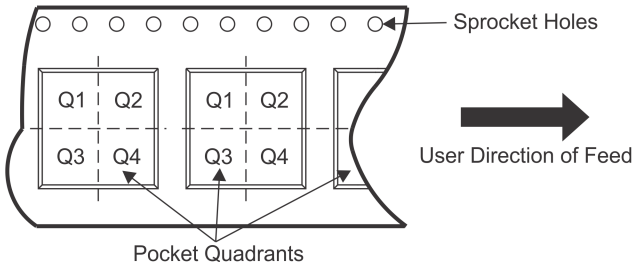


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

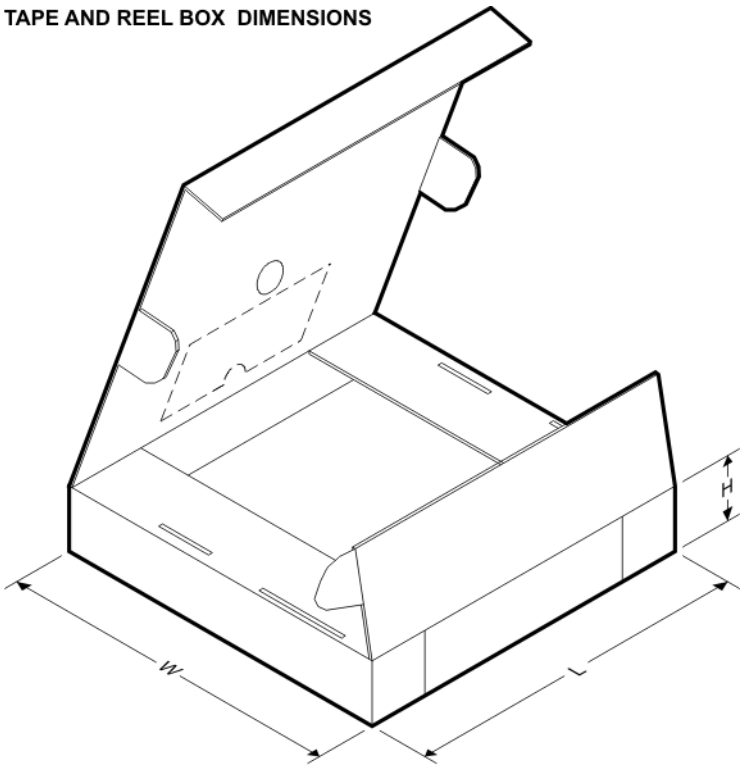
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LMH6639MAX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
LMH6639MF	SOT-23	DBV	6	1000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LMH6639MF/NOPB	SOT-23	DBV	6	1000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LMH6639MFX	SOT-23	DBV	6	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LMH6639MFX/NOPB	SOT-23	DBV	6	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3

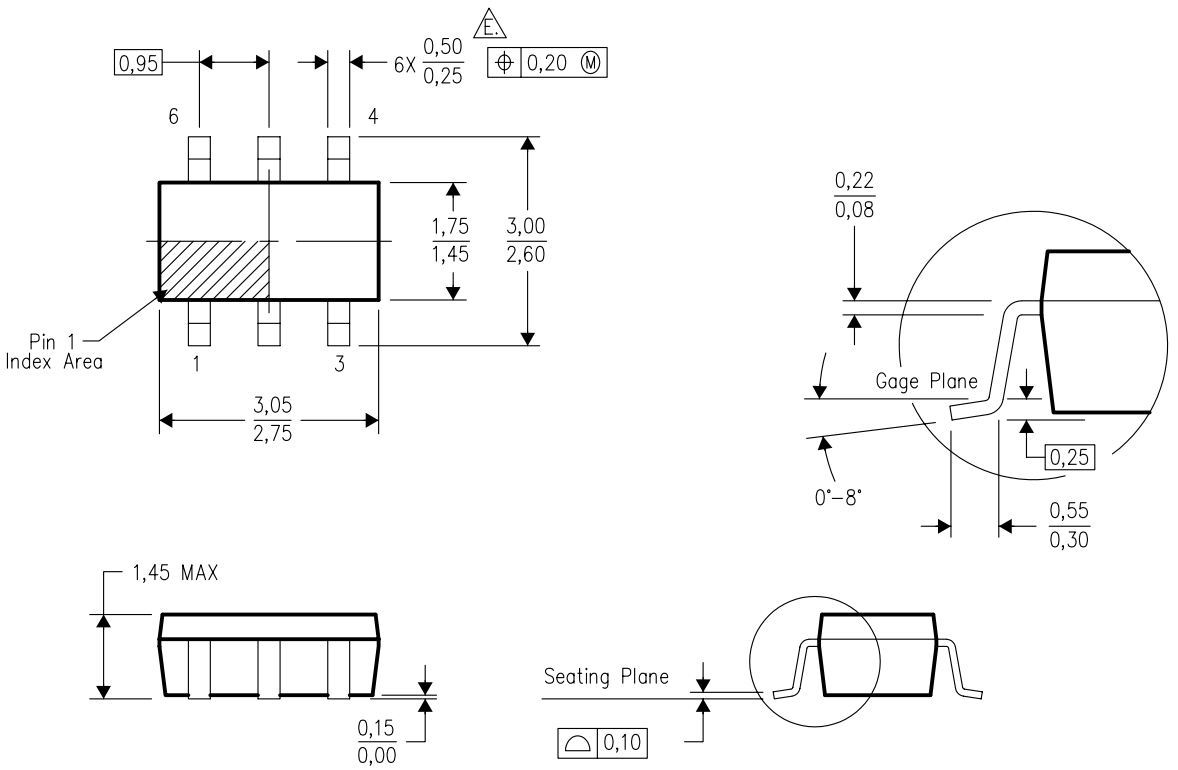
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LMH6639MAX/NOPB	SOIC	D	8	2500	349.0	337.0	45.0
LMH6639MF	SOT-23	DBV	6	1000	203.0	190.0	41.0
LMH6639MF/NOPB	SOT-23	DBV	6	1000	203.0	190.0	41.0
LMH6639MFX	SOT-23	DBV	6	3000	206.0	191.0	90.0
LMH6639MFX/NOPB	SOT-23	DBV	6	3000	206.0	191.0	90.0

DBV (R–PDSO–G6) PLASTIC SMALL–OUTLINE PACKAGE



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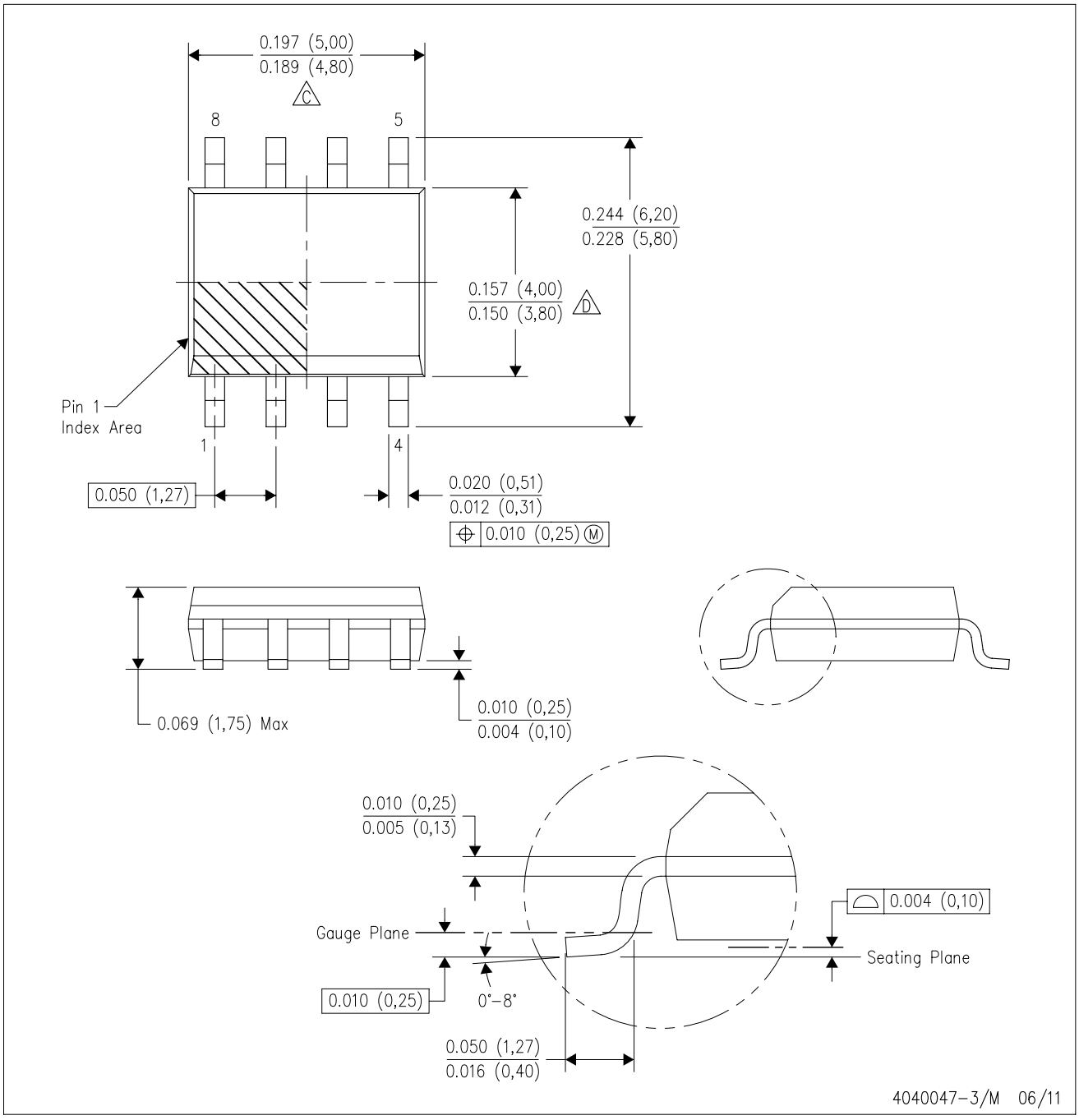
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
E. Falls within JEDEC MO–178 Variation AB, except minimum lead width.

D (R–PDSO–G8) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AA.

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